

Description

The VST10N180 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

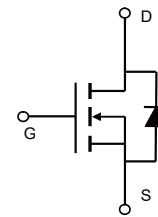
- $V_{DS} = 100V, I_D = 40A$
 $R_{DS(ON)} = 18m\Omega$ (typical) @ $V_{GS} = 10V$
 $R_{DS(ON)} = 22m\Omega$ (typical) @ $V_{GS} = 4.5V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



DFN5x6



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VST10N180	VST10N180-D56	DFN5x6	-	-	-

Absolute Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	40	A
Drain Current-Continuous($T_c = 100^\circ\text{C}$)	$I_D(100^\circ\text{C})$	28.3	A
Pulsed Drain Current	I_{DM}	160	A
Maximum Power Dissipation	P_D	50	W
Derating factor		0.4	W/ $^\circ\text{C}$
Single pulse avalanche energy (Note 1)	E_{AS}	200	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ\text{C}$

Thermal Characteristic

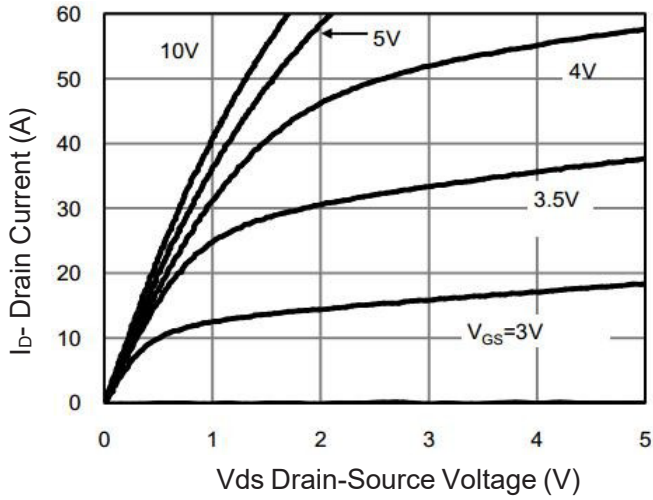
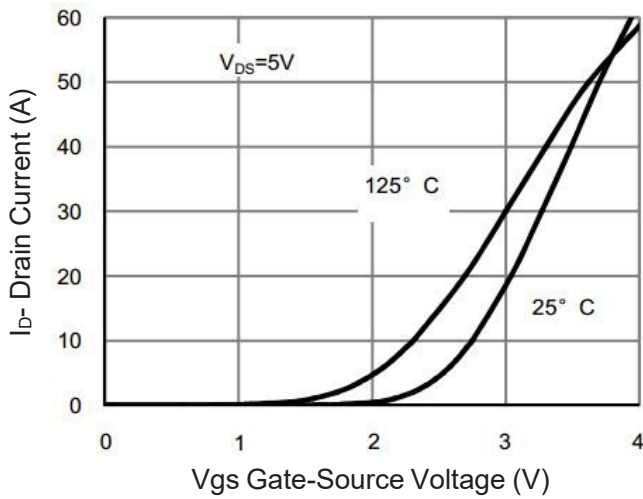
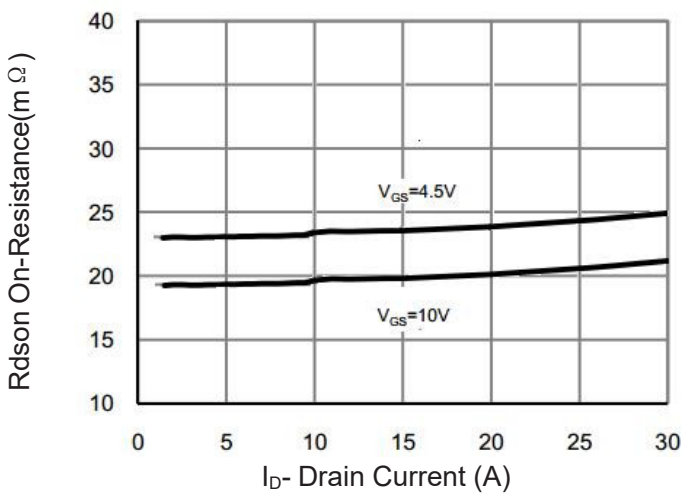
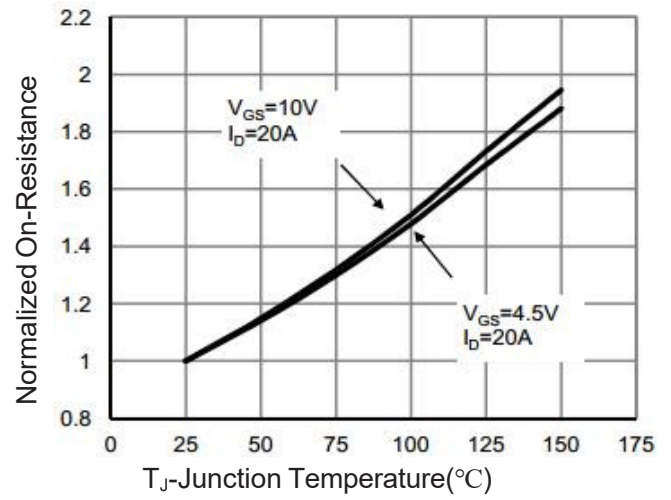
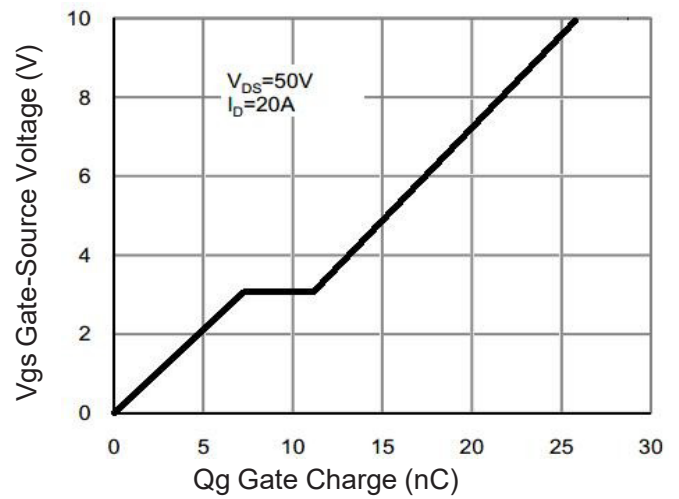
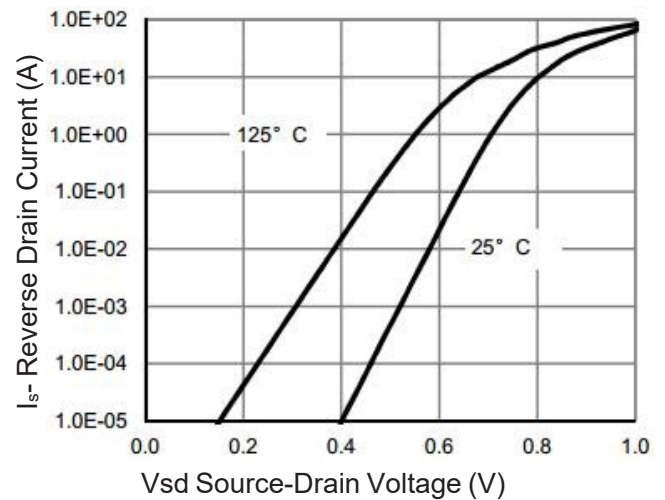
Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	2.5	$^{\circ}\text{C/W}$
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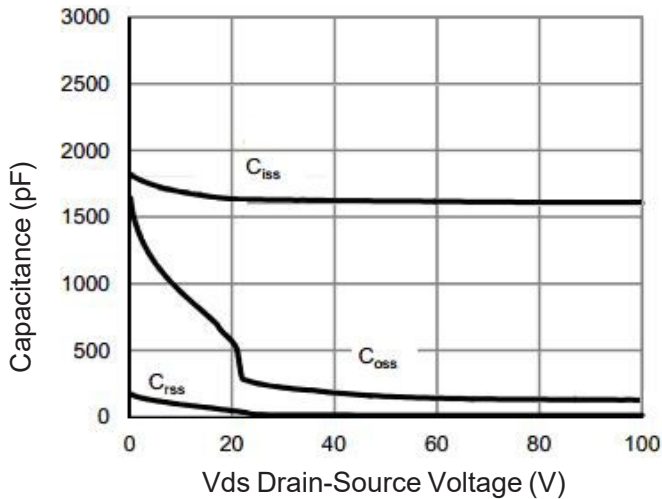
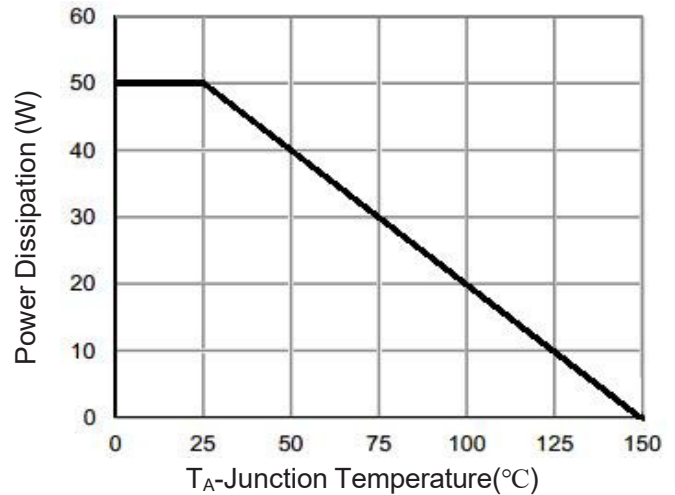
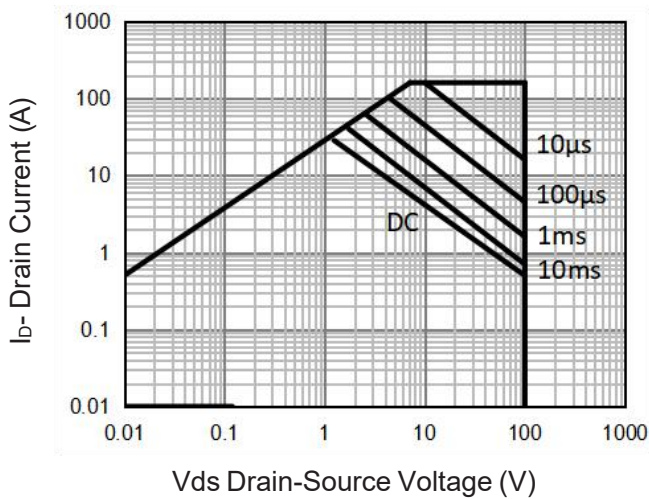
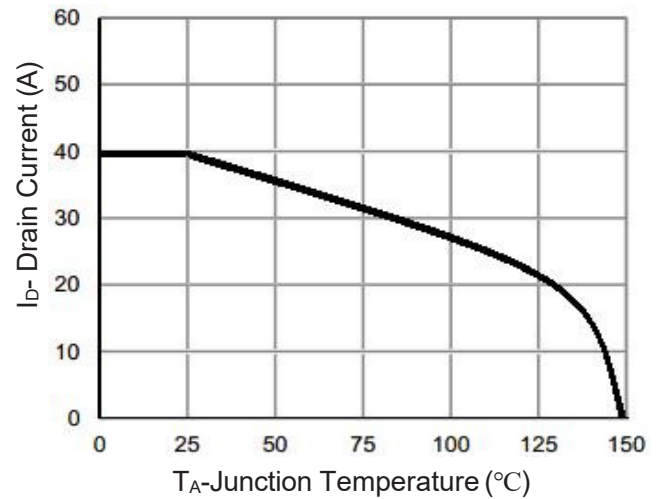
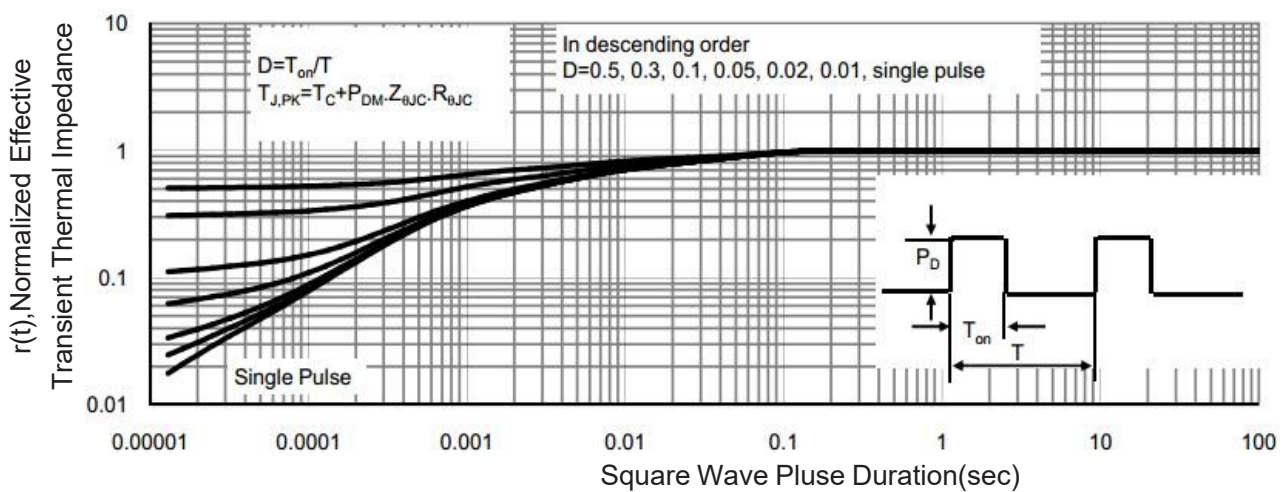
Electrical Characteristics ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	1.2	1.8	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	18	23	mΩ
		V _{GS} =4.5V, I _D =20A	-	22	27	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V,I _D =20A	-	35	-	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =50V,V _{GS} =0V, F=1.0MHz	-	1600	-	PF
Output Capacitance	C _{oss}		-	139	-	PF
Reverse Transfer Capacitance	C _{rss}		-	11	-	PF
Switching Characteristics (Note 2)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =50V,I _D =20A V _{GS} =10V,R _G =1.6Ω	-	6	-	nS
Turn-on Rise Time	t _r		-	2	-	nS
Turn-Off Delay Time	t _{d(off)}		-	18	-	nS
Turn-Off Fall Time	t _f		-	2	-	nS
Total Gate Charge	Q _g	V _{DS} =50V,I _D =20A, V _{GS} =10V	-	26	-	nC
Gate-Source Charge	Q _{gs}		-	7.4		nC
Gate-Drain Charge	Q _{gd}		-	3.8		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =40A	-		1.2	V
Diode Forward Current	I _S		-	-	40	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 20A	-		26	nS
Reverse Recovery Charge	Q _{rr}	di/dt = 500A/μs	-		98	nC

Notes:

1. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=20V, V_G=10V, L=0.5mH, R_G=25\Omega$
2. Guaranteed by design, not subject to production .
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsin k, assuming a maximum junction temperature of $T_J(MAX)=150^{\circ}\text{C}$. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

Figure 2 Transfer Characteristics

Figure 3 Rdson- Drain Current

Figure 4 Rdson-Junction Temperature

Figure 5 Gate Charge

Figure 6 Source- Drain Diode Forward


Figure 7 Capacitance vs Vds

Figure 9 Power De-rating

Figure 8 Safe Operation Area (Note 3)

Figure 10 Current De-rating

Figure 11 Normalized Maximum Transient Thermal Impedance